#### 生长电位对Fe纳米粒子形貌的影响



#### Fe纳米粒子合成条件一形貌全图



#### 不同形貌Fe纳米粒子电催化活性及稳定性研究



The electrocatalytic property of Fe NCs towards Nitrite reduction. (A) *j*-*E* curves recorded on nano-Fe/GC electrodes of Fe NCs with different shape in 0.01 M NaNO<sub>2</sub> + 0.2 M NaOH solution, scan rates 1 mV s<sup>-1</sup>; (B) Steady j-t curves of nitrite reduction on nano-Fe/GC electrodes of Fe NCs of different shape.



Comparison of SEM images of cube Fe NCs before (A) and after (B) electrocatalytic reduction of nitrite.

#### 催化剂表面原子开放度(R)的计算



#### 催化剂表面原子开放度(R)与催化活性之间的关系

Shapes of Fe NCs	bulk-Fe			$\bigcirc$	
R / %		0.77	10.93	40.57	100
$E_{\text{onset}} / V$ (@ $j = -0.07 \text{ mA.cm}^{-2}$ )	-1.181	-1.182	-1.131	-1.093	-1.084
$j/mA.cm^{-2}$ ( @ E = -1.188V, measured from CVs of Fig.4.10A)	-0.40	-0.385	-1.308	-4.32	-6.82
$j/ \text{mA.cm}^{-2}$ ( @ E = -1.188V and t =200 s, measured from Fig.4.10B )	-0.389	-0.261	-1.486	-3.985	-7.126



*j* was measured at –1.188 V in *j-E* curves, the scale bar in all SEM images is 50 nm.

本章小结

- 发展了程序电位阶跃电沉积法,成功地在GC电极表面电沉 积制备了由封闭结构的{110}晶面组成的菱形十二面体和四 方双锥Fe纳米晶体。
- 通过对生长电位(Egrowth)和沉积液浓度的调控,改变了纳 米粒子表面各(hkl)密勒指数二维晶核的生长速度,进而 实现对Fe纳米晶体形状和表面结构的精确调控。
- 结合不同形状Fe纳米粒子,求算其各自的表面原子开放度 (R)。并将R值与其催化活性关联,获得Fe纳米粒子电催化 剂活性随(R)增加而升高的变化规律。



- 1、研究背景介绍
- 2、结果与讨论

(1) 立方体Fe纳米粒子的制备、表征与性能。

- (2) 菱形十二面体、四方双锥和十八面体等一系列Fe纳米 粒子的形貌控制合成。
- (3) 八极子、枝晶和平行连晶形Fe纳米粒子的制备与性能。
- 3、结论

#### 运用二维晶核生长理论指导更开放结构晶面的制备



#### 八极子及枝晶Fe纳米粒子制备与表征



SEM image of Fe NCs electrosynthesized in 0.002 M FeSO<sub>4</sub> + 0.1M Na<sub>2</sub>SO<sub>4</sub> solutions,  $E_{\text{growth}}$ =-1.2V; (a-g)  $t_{\text{growth}}$ =20s; (h-k)  $t_{\text{growth}}$ =60s

#### 蕨状单晶Fe纳米粒子形貌的表征



SEM and TEM images of Fe NCs electrosynthesized in 0.002 M FeSO<sub>4</sub> + 0.1M Na<sub>2</sub>SO<sub>4</sub> solutions,  $E_{\text{growth}}$ =-1.2V;  $t_{\text{growth}}$ =100s

八极子一枝晶Fe纳米粒子生长过程



The relationship between  $t_{\text{growth}}$  and the shapes of the singlecrystalline dendritic Fe Nanostructures

#### 成核时间和成核电位对Fe纳米粒子最终形貌的影响



(a) SEM image of Fe NCs electrosynthesized in 0.002 M FeSO<sub>4</sub> + 0.1M Na<sub>2</sub>SO<sub>4</sub> solutions,  $E_{nuc}$ =-1.4V,  $t_{nuc}$ =2s;  $E_{growth}$ =-0.9V,  $t_{growth}$ =72s; (b,c,e) three typical high magnified SEM images of octapods Fe NCs oriented nearly along the <111>, <110> and <100> axes (d) the geometrical models of octapods Fe NCs; (b-d) three typical high magnified SEM images of octapods Fe NCs oriented nearly along the <110>, <100> and <111> axes; (f,g) TEM image and SAED pattern of octapods Fe NC recorded along <100> direction.

#### 平行连晶Fe纳米粒子生长过程



0.002 M FeSO<sub>4</sub> + 0.1M Na<sub>2</sub>SO<sub>4</sub> solutions,  $E_{nuc}$ =-1.4V,  $t_{nuc}$ =2s;  $E_{growth}$ =-0.9V,  $t_{growth}$ =140s;



0.002 M FeSO<sub>4</sub> + 0.1M Na<sub>2</sub>SO<sub>4</sub> solutions,  $E_{nuc}$ =-1.4V,  $t_{nuc}$ =2s;  $E_{growth}$ =-0.9V,  $t_{growth}$ =380s;

#### 八极子一平行连晶Fe纳米粒子生长过程



The relationship between  $t_{\text{growth}}$  ( $E_{\text{nuc}}$ =-1.4V,  $t_{\text{nuc}}$ =-2s); and the shapes of the single-crystalline parallel intergrouth Fe Nanostructures

枝晶,平行连晶Fe纳米粒子催化活性研究



The electrocatalytic property of Fe NCs towards Nitrite reduction. *j-E* curves recorded on nano-Fe/GC electrodes of Fe NCs with different shape in 0.01 M NaNO<sub>2</sub> + 0.2 M NaOH solution, scan rates 1 mV s<sup>-1</sup>.

## 结

### 论

- 用CV和CA电沉积的方法,在玻碳(GC)基底上制备具有立方体结构 的Fe单晶纳米粒子。并实现了对其粒径的控制。
- 2. 建立了对纳米Fe电极活化表面积的标定方法。
- 发展程序电位阶跃电沉积方法,系统地实现了对Fe纳米晶体形状和表面结构的精确调控。成功地制备出具有完美晶型的菱形十二面体、四方双锥、一系列十八面体,以及立方体Fe单晶纳米粒子。
- 运用程序电位阶跃电沉积法,成功地在GC电极表面电沉积制备了枝晶 和平行连晶等单晶Fe纳米材料,并系统地研究了其生长过程。
- 5. 所制备的各种形貌Fe纳米粒子的电催化活性研究结论如下:

枝晶>平行连晶>立方体>十八面体>菱形十二面体 ~ 四方双锥 ~ 本体Fe

本论文的研究结果不仅从实验上验证了二维晶核生长理论。而且进 一步证明在实现纳米催化剂形状控制与合成的征程中,电化学法是一种 非常有效的方法。它为合成和制备更多、更高效的催化剂提供了有效的 途径。



# 京心感谢导师孙世刚教授的悉心指导和裁培! 感谢SG405课题组老师们的关心与厚爱! 感谢电学教研室全体老师的支持与帮助! 感谢所有帮助、支持过我的老师和同学们!

# *感谢答辩委员会各位老师的莅临! 敬请指正!*

#### 纳米Fe电极活性面积标定方法介绍



Cyclic voltammograms of bulk Fe (a) and cube nm-Fe/GC (b) electrodes, 0.2 M NaOH solution, scan rate 25 mV s<sup>-1</sup>, with potential scan range between -1.1 and -0.5V.